



# CMOS 12-Bit Monolithic Multiplying DAC

**AD7541A**

T-51-09-12

**1.1 Scope.**

This specification covers the detail requirements for a 12-bit monolithic CMOS multiplying digital-to-analog converter. The AD7541A is a direct replacement for the industry standard AD7541, offering improved performance in the areas of latch-up, lower gain error and gain temperature coefficient.

**1.2 Part Number.**

The complete part number per Table 1 of this specification is as follows:

Device	Part Number <sup>1</sup>
-1	AD7541AS(X)/883B
-2	AD7541AT(X)/883B

**NOTE**

<sup>1</sup>See paragraph 1.2.3 for package identifier.

**1.2.3 Case Outline.**

See Appendix 1 of General Specification ADI-M-1000: package outline:

(X)	Package	Description
Q	Q-18	18-Pin Cerdip
E	E-20A	20-Contact LCC

**1.3 Absolute Maximum Ratings.** ( $T_A = 25^\circ\text{C}$  unless otherwise noted. Pin numbers refer to DIP package.)

$V_{DD}$ (Pin 16) to GND	+17V
$V_{REF}$ (Pin 17) to GND	$\pm 25\text{V}$
$V_{RFB}$ (Pin 18) to GND	$\pm 25\text{V}$
Digital Input Voltage (Pin 4–Pin 15) to GND	$-0.3\text{V}, V_{DD}$
$V_{PIN1}, V_{PIN2}$ to GND	$-0.3\text{V}$ to $V_{DD}$
<b>Power Dissipation</b>	
Up to $+75^\circ\text{C}$	450mW
Derates above $+75^\circ\text{C}$	6mW/ $^\circ\text{C}$
Operating Temperature Range	$-55^\circ\text{C}$ to $+125^\circ\text{C}$
Storage Temperature Range	$-65^\circ\text{C}$ to $+150^\circ\text{C}$

**1.5 Thermal Characteristics.**

Thermal Resistance  $\theta_{JC} = 35^\circ\text{C}/\text{W}$  for Q-18 and E-20A  
 $\theta_{JA} = 120^\circ\text{C}/\text{W}$  for Q-18 and E-20A

## AD7541A — SPECIFICATIONS

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Test	Symbol	Device	Design Limit @ +125°C	Sub Group 1	Sub Group 2, 3	Sub Group 4	Test Condition <sup>1</sup>	Units
Resolution	RES	-1, 2	12					Bits
Relative Accuracy	RA	-1	1	1	1			± LSB max
		-2	1/2	1	1/2	1/2		
Differential Nonlinearity	DNL	-1	1	1	1		All Grades Guaranteed Monotonic to 12 Bits, T <sub>min</sub> to T <sub>max</sub>	± LSB
		-2	1/2	1	1/2	1/2		
Gain Error <sup>2</sup>	AE	-1	8	6	8			± LSB max
		-2	5	6	5	3		
Gain Tempco	TC <sub>AE</sub>	-1, 2	5					± ppm/°C max
Power Supply Rejection	PSRR	-1, 2	0.02	0.01	0.02		ΔV <sub>DD</sub> = ± 5%	± % per % max
Output Leakage Current Pin 1 Pin 2	I <sub>OUT1</sub>	-1, 2	200	5	200		Digital Inputs = 0V Digital Inputs = V <sub>DD</sub>	± nA max
	I <sub>OUT2</sub>	-1, 2	200	5	200			± nA max
Output Current Settling Time		-1, 2	0.6				To ± 1/2LSB, R <sub>OUT1</sub> = 100Ω, C <sub>OUT1</sub> = 13pF Digital Inputs = V <sub>IH</sub> to V <sub>IL</sub> or V <sub>IL</sub> to V <sub>IH</sub>	μs typ
Feedthrough Error <sup>3</sup>	FT	-1, 2	1				V <sub>REF</sub> = ± 10V 10kHz Sinewave T <sub>A</sub> = +25°C	mV p-p typ
Reference Input Resistance	R <sub>IN</sub>	-1, 2	7	7	7			kΩ min
		-1, 2	18	18	18			kΩ max
Digital Input High Voltage	V <sub>IH</sub>	-1, 2	2.4	2.4	2.4			V min
Digital Input Low Voltage	V <sub>IL</sub>	-1, 2	0.8	0.8	0.8			V max
Digital Input Leakage Current	I <sub>IN</sub>	-1, 2	1	1	1		V <sub>IN</sub> = 0V or V <sub>DD</sub>	± μA max
Digital Input Capacitance	C <sub>IN</sub>	-1, 2	8					pF max
Output Capacitance Pin 1 Pin 2	C <sub>OUT1</sub>	-1, 2	200				Digital Inputs = V <sub>IH</sub> Digital Inputs = V <sub>IH</sub>	pF max
	C <sub>OUT2</sub>	-1, 2	70					pF max
Output Capacitance Pin 1 Pin 2	C <sub>OUT1</sub>	-1, 2	70				Digital Inputs = V <sub>IL</sub> Digital Inputs = V <sub>IL</sub>	pF max
	C <sub>OUT2</sub>	-1, 2	200					pF max
Supply Current from V <sub>DD</sub>	I <sub>DD</sub>	-1, 2	2	2	2		Digital Inputs = V <sub>IH</sub> or V <sub>IL</sub> Digital Inputs = 0V or V <sub>DD</sub>	mA max
			500	100	500			μA max

## NOTES

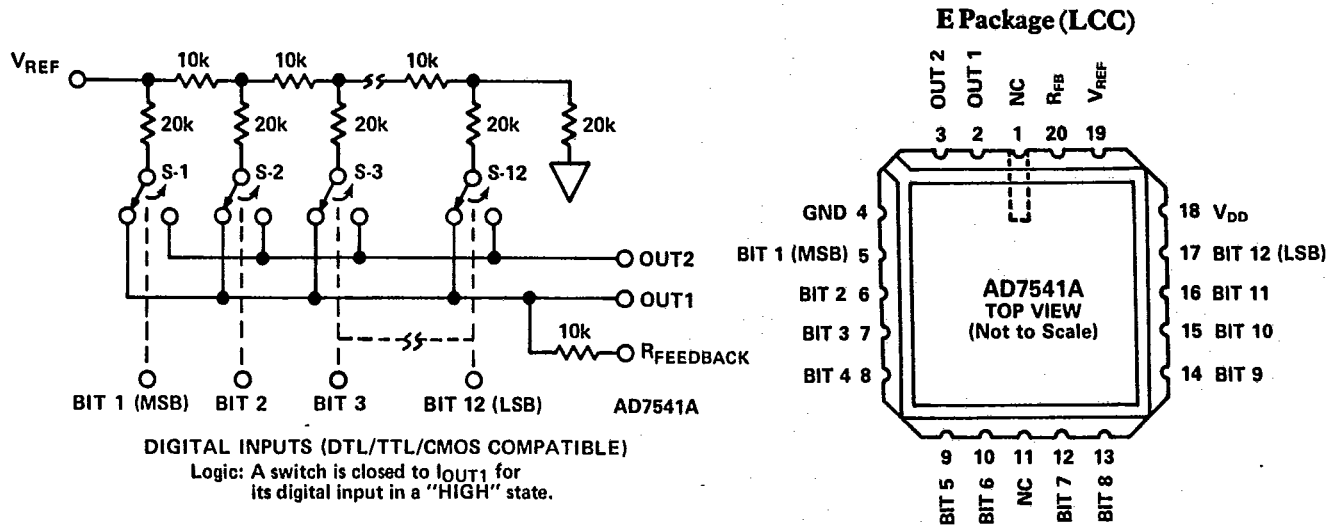
<sup>1</sup>V<sub>DD</sub> = +15V; V<sub>OUT1</sub> = V<sub>OUT2</sub> = 0V; V<sub>REF</sub> = +10V unless otherwise stated.<sup>2</sup>Measured using internal feedback resistor and includes effect of leakage current and gain TC.<sup>3</sup>Feedthrough error can be reduced by connecting the lid of the ceramic package to ground.

Table 1.

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### 3.2.1 Functional Block Diagram and Terminal Assignments.



### 3.2.4 Microcircuit Technology Group.

This microcircuit is covered by technology group (80).

### 4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).

